DECLARATION FOR PATENT APPLICATION

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled:

SELF ALIGNED METHOD OF FORMING A SEMICONDUCTOR MEMORY ARRAY OF FLOATING GATE MEMORY CELLS WITH LOW RESISTANCE SOURCE REGIONS AND HIGH SOURCE COUPLING, AND A MEMORY ARRAY MADE THERBY

the specification of which (check one) is attached hereto or _X was filed on <u>July 26, 2001</u> as Application No. <u>09/916,555</u> and was amended on (if applicable).				
	re reviewed and understand s amended by any amendme	the contents of the above-identified specification, ent referred to above.		
I acknowledge the duty to disclose all information which is material to patentability as defined in 37 CFR § 1.56.				
application(s) for pater designated at least one	it or inventor's certificate, o country other than the Unit for patent or inventor's cer	J.S.C. § 119(a)-(d) or § 365(b) of any foreign or § 365(a) of any PCT International application which ted States, listed below and have also identified below tificate having a filing date before that of the application		
Prior Foreign Applicati	ion(s)	Priority Claimed Yes No		
Number	Country	Day/Month/Year Filed		
I hereby claim the bene 60/234,314	efit under 35 U.S.C. § 119(a	e) of any United States provisional application(s) below.		
Application Number	Filing Date	, 2000		
60/242,096	October 19, 20	000		
Application Number	Filing Date			
60/260,167	January 5, 200			
Application Number	Filing Date			
60/275,517	March 12, 200			
Application Number	Filing Date			
_60/287,047	April 26, 2001	ı		

I hereby claim the benefit under 35 U.S.C. § 120 of any United States application(s), or § 365(c) of any PCT International application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of 35 U.S.C. § 112, I acknowledge the duty to disclose all information which is material to patentability as defined in 37 CFR § 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application:

Application Number	Filing Date	Status: Patented, Pending, Abandoned
		1
Application Number	Filing Date	Status: Patented, Pending, Abandoned
on information and belief a knowledge that willful fals	are believed to be true se statements and the 101 and that such will:	of my own knowledge are true and that all statements made; and further that these statements were made with the like so made are punishable by fine or imprisonment or ful false statements may jeopardize the validity of the
Full name of sole or first is	nventor <u>Ch</u>	ih Hsin Wang
Inventor's signature	Ch Je	Hang 8/31/01
D:4 (505 C)		Date
Residence 6585 Gi Citizenship. Taiwan	llis Drive, San Jose, C	A 95120 1
Post Office Address	6585 Gillis Drive, Sa	an Jose CA 95120
4-		
Full name of second inven	itor <u>An</u>	nitay Levi
Inventor's signature	Lande	8/3 i 0) Date
Residence 20833 C	Greenleaf Drive, Cupe	
Citizenship. U.S.A.		
Post Office Address	20833 Greenleaf Dri	ve, Cupertino, CA 95014